

TOSHIBA Photocoupler GaAlAs Ired + Photo IC

TLP759(IGM)

Transistor Invertor Inverter For Air Conditioner Line Receiver IPM Interfaces

The TOSHIBA TLP759 (IGM) consists of a GaAtAs high–output light emitting diode and a high speed detector of one chip photo diode transistor.

This unit is 8-lead DIP.

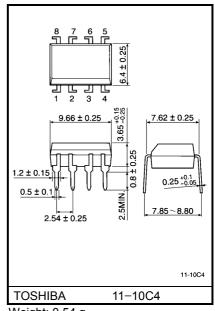
TLP759(IGM) has no internal base connection, and a faraday shield integrated on the photodetector chip provides an effective common mode noise transient immunity.

TLP759(IGM) guarantees minimum and maximum of propagation delay time, switching time dispersion, and high common mode transient immunity. Therefor TLP759(IGM) is suitable for isolation interface between IPM(intelligent power module) and control IC circuits in motor control application.

- Isolation voltage: 5000V_{rms} (min.)
- Common mode transient immunity : ±10kV / μs (min.)
 @V_{CM} = 1500 V
- Switching Time
 t_{pHL},t_{pLH} = 0.1µs (min.)
 = 0.8µs (max.)

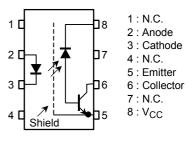
 $@I_F = 10 \text{mA}, \text{VCC} = 15 \text{V}, \text{RL} = 20 \text{k}\Omega, \text{Ta} = 25^{\circ}\text{C}$

- Switching time dispersion: 0.7µs (max.) (|tpLH-tpHL|)
- TTL compatible
- UL recognized: UL1577, file no.E67349

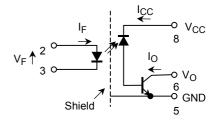


Weight: 0.54 g

Pin Configuration(top view)



Schematic



Unit in mm

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 Option (D4) type VDE approved: DIN VDE0884 / 06.92, Maximum operating insulation voltage: 890VPK Highest permissible over voltage: 6000VPK

(Note 1) When a VDE0884 approved type is needed, please designate the "Option (D4)"

• Structural parameter 7.62mm pich TLP759 (IGM) Creepage distance: 7.0mm (min.) Clearance: 7.0mm (min.) Insulation thickness: 0.4mm (min.)

Maximum Ratings (Ta = 25°C)

	Characteristic		Symbol	Rating	Unit
	Forward current	(Note 2)	١ _F	25	mA
	Pulse forward current	(Note 3)	I _{FP}	50	mA
LED	Peak transient forward current	(Note 4)	I _{FPT}	1	А
	Reverse voltage		VR	5	V
	Diode power dissipation	(Note 5)	PD	45	mW
Detector	Output current		Ι _Ο	8	mA
	Peak output current		I _{OP}	16	mA
	Output voltage		Vo	-0.5~20	V
ð	supply voltage		V _{CC}	-0.5~30	V
	Output power dissipation	(Note 6)	PO	100	mW
Оре	Operating temperature range		T _{opr}	-55~100	°C
Stor	age temperature range	T _{stg}	-55~125	°C	
Lea	Lead solder temperature(10s) (Note 7)		T _{sol}	260	°C
Isola	ation voltage(AC,1min.,R.H.≤60%,Ta=25°C)	BVS	5000	V _{rms}	

(Note 2): Derate 0.8mA above 70°C.

(Note 3): 50% duty cycle, 1ms pulse width.

Derate 1.6mA / °C above 70°C.

(Note 4): Pulse width PW \leq 1µs,300pps.

(Note 5): Derate 0.9mW / °C above 70°C.

(Note 6): Derate 2mW / °C above 70°C.

(Note 7): Soldering portion of lead: Up to 2mm from the body of the device.

(Note 8): Device considerd a two terminal device: Pins 1, 2, 3 and 4 shorted together and

pins 5, 6, 7 and 8 shorted together.

Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	V _F	I _F = 16mA		1.65	1.85	V
LED	Forward voltage temperature coefficient	ΔV _F /ΔTa	I _F = 16mA		-2	_	mV / °C
	Reverse current	I _R	V _R = 5V		—	10	μA
	Capacitance between terminal	CT	V _F = 0,f = 1MHz	_	45	_	pF
Detector	High level output current	I _{OH (1)}	$I_{F} = 0mA, V_{CC} = V_{O} = 5.5V$	_	3	500	nA
		I _{OH (2)}	$I_{F} = 0mA, V_{CC} = 30V$ $V_{O} = 20V$	_	_	5	
		IOH	$I_F = 0mA, V_{CC} = 30V$ $V_O = 20V, Ta = 70^{\circ}C$	_	_	50	μA
	High level supply voltage	ICCH	I _F = 0mA,V _{CC} = 30V	_	0.01	1	μA
	Supply voltage	V _{CC}	I _{CC} = 0.01mA	30	_	—	V
	Output voltage	Vo	I _O = 0.5mA	20	_	_	V

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Current transfer ratio	lo / la	$I_F = 10mA, V_{CC} = 4.5V$ $V_O = 0.4V$	25	35	75	. %
	I _O / I _F	I _F = 16mA,V _{CC} = 4.5V V _O = 0.4V,Ta = -25~100°C	15	_	_	
Low level output voltage	V _{OL}	I _F = 16mA,V _{CC} = 4.5V I _O = 2.4mA	_	_	0.4	V

Isolation Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	C _S	V = 0,f = 1MHz (Note 8)	_	0.8		pF
Isolation resistance	R _S	R.H. ≤ 60%,V _S = 500V (Note 8)	1×10 ¹²	10 ¹⁴	_	Ω
		AC,1 minute	5000	-	_	V _{rms}
Isolation voltage	BVS	AC,1 second,in oil	_	10000	_	Vdc
		DC,1 minute,in oil		10000		vuc

Switching Characteristics (Ta = 25°C,V_{CC} = 15V)

Characteristic		Symbol	Test Cir– cuit	Test Condition	Min.	Тур.	Max.	Unit
Propagation delay time	tion delay time	t _{pHL}	- 1 -	$I_F = 10mA, R_L = 20k\Omega$	0.1	0.45	0.8	μs
(H→L)				I _F = 10mA,R _L = 20kΩ Ta = 0~85°C	0.1	0.45	0.9	
Propagation delay time (L→H)		^t pLH		I _F = 10mA,R _L = 20kΩ Ta = -25~100°C	0.1	0.45	1.0	
		t _{pLH} -t _{pHL}		$I_F = 10 \text{mA}, \text{R}_L = 20 \text{k}\Omega$	_	0.15	0.7	μs
Switching time dispersion between on				I _F = 10mA,R _L = 20kΩ Ta = 0~85°C	_	0.25	0.8	
and off				I _F = 10mA,R _L = 20kΩ Ta = -25~100°C	_	0.25	0.9	
Common mode transient immunity at logic high output	(Note 9)	CM _H	2	$I_F = 0mA$ V _{CM} = 1500V _{p-p} R _L = 20kΩ	10000	15000	_	V / µs
Common mode transient immunity at logic low output	(Note 9)	CML		I_F =10mA V _{CM} = 1500V _{p-p} R _L = 20kΩ	-10000	-15000	_	V / µs

(Note 9): CM_{L} is the maximum rate of fall of the common mode voltage that can be

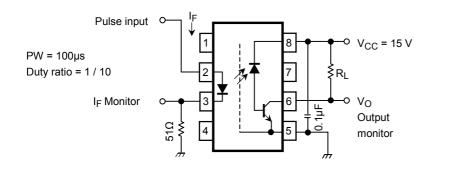
sustained with the output voltage in the logic low state($V_O < 1V$).

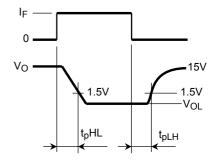
 $\ensuremath{\mathsf{CM}}_H$ is the maximum rate of rise of the common mode voltage that can be

sustained with the output voltage in the logic high state(V_O < 4V).

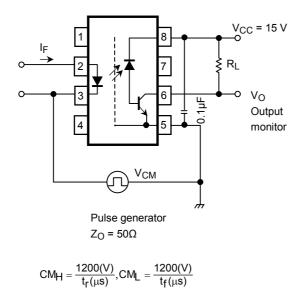
(Note 10): Maximum electrostatic discharge voltage for any pins: 100V(C = 200pF, R = 0).

Test Circuit 1: Switching Time Test Circuit

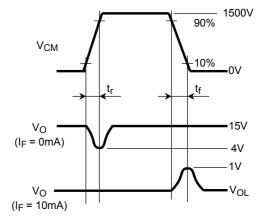




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Test Circuit 2: Common Mode Noise Immunity Test Circuit



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